



# SILICON PLANAR EPITAXIAL TRANSISTORS

# BC327/A BC328 PNP BC337/A BC338 NPN

**TO-92** 



Plastic Package RoHS compliant

TO-92

### FEATURE:

1. This product is available in AEC-Q101 Qualified and PPAP Capable also. **Note:** For AEC-Q101 qualified products, please use suffix -AQ in the part number while ordering.

### **APPLICATIONS:**

General Purpose Transistors Best Suited for use in Driver and Output Stages of Audio Amplifier

### PARAMETER SYMBOL BC327/337 BC327A/337A BC328/338 UNIT Collector Emitter Voltage 45 60 25 V<sub>CEO</sub> V 50 60 V Collector Emitter Voltage 30 $V_{CES}$ V<sub>EBO</sub> V Emitter Base Voltage 5 **Collector Current Continuous** 800 mΑ $I_{\rm C}$ **Collector Current Peak** 1000 mΑ I<sub>CM</sub> **Emitter Current Peak** 1000 mΑ $I_{EM}$ Base Current Continuous 100 $I_{B}$ mΑ **Base Current Peak** 200 $I_{BM}$ mΑ Power Dissipation at Ta=25°C 625 mW $\mathsf{P}_\mathsf{D}$ Derate Above 25°C mW/°C 5 **Operating And Storage Junction** °C -65 to +150 T<sub>i</sub>, T<sub>stq</sub> Temperature Range

# **ABSOLUTE MAXIMUM RATINGS** (Ta = 25 °C Unless otherwise specified)

# THERMAL RESISTANCE

Junction to Ambient in free air	R <sub>th (j-a)</sub>	200	°C/W
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An IATF 16949, ISO9001 and ISO 14001/ISO 45001 Certified Company

ELECTRICAL CHARACTERISTICS at (Ta = 25 °C Unless otherwise specified)								
PARAMETER	SYMBOL	TEST C	ONDITION	IS	MIN	TYP	MAX	UNIT
Collector Emitter Voltage	V <sub>CEO</sub>	EO I <sub>C</sub> =1mA, -	BC327/	/337	45			V
			BC327A	′337A	60			V
			BC328/	/338	25			V
		I <sub>c</sub> =100m A,	BC327/	/337	50			V
Collector Emitter Voltage	V <sub>CES</sub>	Ũ	BC327A		60			V
		I <sub>E</sub> =0	BC328/	/338	30			V
Emitter Base Voltage	$V_{EBO}$	I <sub>E</sub> =10	m A, I <sub>C</sub> =0		5.0			V
Collector Cut Off Current	I <sub>CBO</sub>	V <sub>CB</sub> =2	20V, I <sub>E</sub> =0,				100	nA
		V <sub>CB</sub> =20V, I	<sub>E</sub> =0, T <sub>J</sub> =15	0°C			5	μA
Emitter Cut Off Current	I <sub>EBO</sub>	V <sub>EB</sub> =	=5V, I <sub>C</sub> =0				10	μA
Collector Emitter Saturation Voltage	V <sub>CE (sat)</sub> <sup>1</sup>	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA				0.7	V	
Base Emitter On Voltage	$V_{BE(on)}{}^1$	I <sub>C</sub> =500mA, V <sub>CE</sub> =1V				1.2	V	
		I <sub>c</sub> =100mA,	BC327A	′337A	100		400	
		V=1V	BC327/	328,	100		600	
		BC327/328 BC337/338	Group-10		63		160	
DC Current Gain	h <sub>FE</sub>		Group-16		100		250	
			Group		160		400	
			Group-40		250		600	
		I <sub>C</sub> =500r	nA, V <sub>CE</sub> =1'	V	40			
SMALL SIGNAL CHARACTERISTICS								
<b>-</b> · · · <b>-</b>	f <sub>T</sub>	I <sub>c</sub> =10mA, <sup>v</sup>	V <sub>CE</sub> =5V.	NPN		200		MHz
Transistors Frequency		f=35MHz		PNP		100		MHz
		$v_{CB}$ 10 $v$ , $i_E$ -0,		NPN		5		pF
Output Capacitance	C <sub>ob</sub>			PNP		8		pF

# ELECTRICAL CHARACTERISTICS at (Ta = 25 °C Unless otherwise specified)

Note:

2. For PNP device voltage and current values will be negative (-).

<sup>1.</sup> Pulse Condition: Pulse Width  $\leq$ 300us, Duty Cycle  $\leq$ 2%.



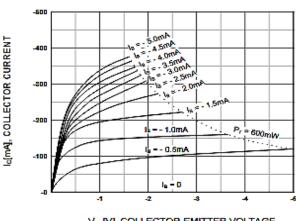


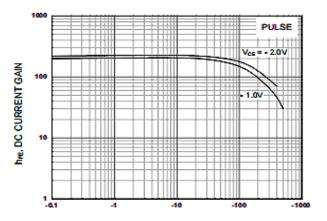
10µÅ

V<sub>cE</sub>[V], COLLECTOR-EMITTER VOLTAGE

# **TYPICAL CHARACTERISTICS CURVES**

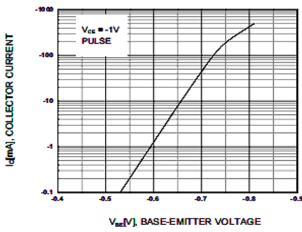
Fig 1: Static Characteristic





Ic[mA], COLLECTOR CURRENT

Fig 3: Base-Emitter On Voltage

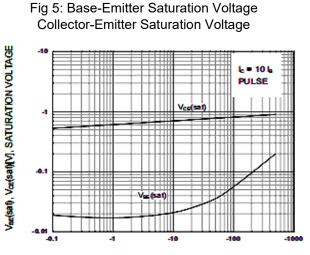


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Fig 4: Static Characteristic ليري Domy -12 ŝ

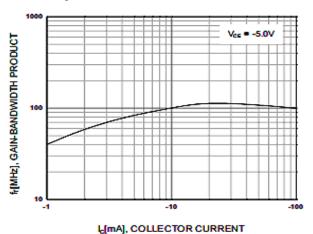
-10

I, [mA], COLLECTOR CURRENT



Ic[mA], COLLECTOR CURRENT

### Fig 6: Gain Bandwidth Product

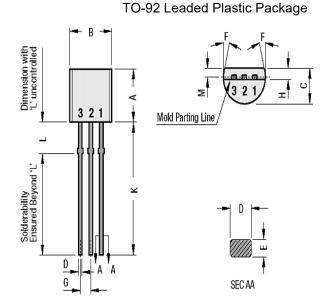


Vcs[V], COLLECTOR-EMITTER VOLTAGE

### Fig 2: DC current Gain



# PACKAGE DETAILS



DIM	MIN	MAX
Α	4.32	5.33
В	4.45	5.20
С	3.18	4.19
D	0.40	0.55
Е	0.30	0.55
F		5°
G	1.14	1.40
Н	1.20	1.40
K	12.7	
L	1.982	2.082
М	1.03	1.20

All dimensions are in mm

## **PIN CONFIGURATION**

- 1. Emitter
- 2. Base
- 3. Collector

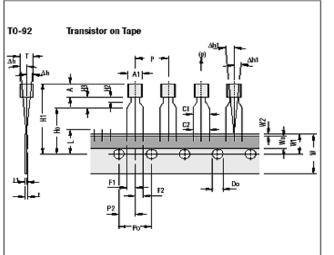




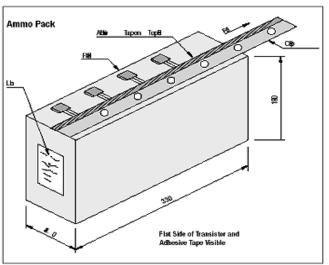


## **Packaging Information**

Package/Case		Std. Packing	ing Inner Carton			Outer Carton		
Туре	Packaging Type	Qty	Qty	Size L x W x H	Gross Weight	Qty	Size L x W x H	Gross Weight
туре		wy	wiy	(cm)	(Kg)	wiy	(cm)	(Kg)
TO-92	Bulk	1,000	5K	19x19x8	1.10	80K	43x40x35	20.0
10-52	T&A	2,000	2K	32x4.5x20	0.70	40K	43x40x35	15.20



# TO-92 Tape and Ammo Packaging



# **Tape Specifications**

Item description	Symbol
Body width	A1
Body height	A
Body thickness	T
Pitch of component <sup>Cr</sup>	Р
Feed hole pitch <sup>\$1</sup>	Po
Feed hole center to	
component centre52	P2
Comp. alignment, Side view <sup>§3</sup>	Dh
Comp. alignment, Front view <sup>53</sup>	Dh1
Tape width <sup>Cr</sup>	W
Hold down tape width <sup>Cr</sup>	Wo
Hole position	W1
Hold-down tape position	W2
Lead wire clinch height	Ho
Component height	H1
Length of snipped leads	L
Feed hole diameter <sup>Cr</sup>	Do
Total tape thickness <sup>§4</sup>	t
Lead-to-lead distance <sup>Cr</sup>	F1, F2
Stand off	H2
Clinch height	H3
Lead parallelismCr	C1-C2
Pull-out force	(p)

All Dimensions are in mm BC327\_338 Rev0504082023EM

T0-92			
Min	Nom	Max	Tol
4.45		5.20	
4.32		5.33	
3.18		4.19	
	12.7		±1.0
	12.7		±0.3
	6.35		±0.4
	0	1.0	
	0	1.3	
	18		±0.5
	6		±0.2
	9		+0.7 -0.5
0.0		0.7	
	16		±0.5
		24.0	
		11.0	
	4		±0.2
		1.2	
2.4		2.7	
0.45		1.45	
		3.0	
		0.22	
6N			

### Taping Specification

- Maximum alignment deviation between leads not to be greater than 0.20 mm.
- Maximum non-cumulative variation between tape feed holes shall not exceed 1 mm in 20 pitches.
- Hold down tape not to exceed beyond the edge(s) carrier tape and there shall be no exposure of achesive.
- No more than 3 consecutive missing components is permitted.
- A tape trailer, having at least three feed holes is required after the last component.
- Splices shall not interfere with the sprocket feed holes.
- §1 Cumulative pitch error 1.0 mm/20 pitch.
- §2 To be measured at bottom of clinch.
- §3 At top of body.
- §4 t1 = 0.3 0.6 mm
- Cr Critical Dimension.



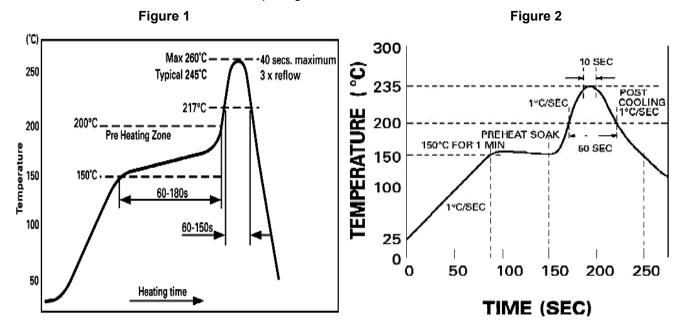


### **Recommended Reflow Solder Profiles**

The recommended reflow solder profiles for Pb and Pb-free devices are shown below.

Figure 1 shows the recommended solder profile for devices that have Pb-free terminal plating, and where a Pb-free solder is used.

Figure 2 shows the recommended solder profile for devices with Pb-free terminal plating used with leaded solder, or for devices with leaded terminal plating used with a leaded solder.



### Reflow profiles in tabular form

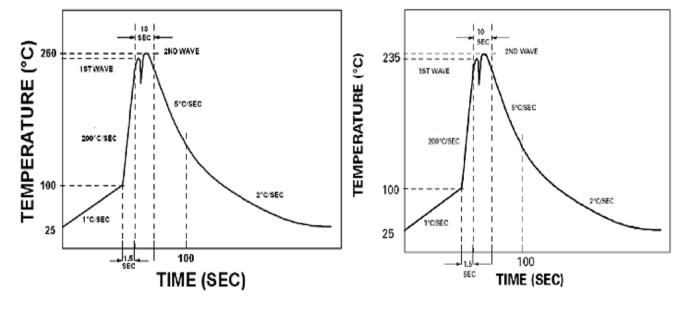
Profile Feature	Sn-Pb System	Pb-Free System
Average Ramp-Up Rate	~3°C/second	~3°C/second
<b>Preheat</b> – Temperature Range – Time	150-170°C 60-180 seconds	150-200°C 60-180 seconds
Time maintained above: – Temperature – Time	200°C 30-50 seconds	217°C 60-150 seconds
Peak Temperature	235°C	260°C max.
Time within +0 -5°C of actual Peak	10 seconds	40 seconds
Ramp-Down Rate	3°C/second max.	6°C/second max.





### **Recommended Wave Solder Profiles**

The Recommended solder Profile For Devices with Pb-free terminal plating where a Pb-free solder is used The Recommended solder Profile For Devices with Pb-free terminal plating used with leaded solder, or for devices with leaded terminal plating used with leaded solder



### Wave Profiles in Tabular Form

Profile Feature	Sn-Pb System	Pb-Free System
Average Ramp-Up Rate	~200°C/second	~200°C/second
Heating rate during preheat	Typical 1-2, Max 4°C/sec	Typical 1-2, Max 4°C/Sec
Final preheat Temperature	Within 125°C of Solder Temp	Within 125°C of Solder Temp
Peak Temperature	235°C	260°C max.
Time within +0 -5°C of actual Peak	10 seconds	10 seconds
Ramp-Down Rate	5°C/second max.	5°C/second max





# Recommended Product Storage Environment for Discrete Semiconductor Devices

This storage environment assumes that the Diodes and transistors are packed properly inside the original packing supplied by CDIL.

- · Temperature 5 °C to 30 °C
- · Humidity between 40 to 70 %RH
- · Air should be clean.
- · Avoid harmful gas or dust.
- $\cdot$  Avoid outdoor exposure or storage in areas subject to rain or water spraying .
- Avoid storage in areas subject to corrosive gas or dust. Product shall not be stored in areas exposed to direct sunlight.
- · Avoid rapid change of temperature.
- · Avoid condensation.
- $\cdot\,$  Mechanical stress such as vibration and impact shall be avoided.
- · The product shall not be placed directly on the floor.
- The product shall be stored on a plane area. They should not be turned upside down. They should not be placed against the wall.

### Shelf Life of CDIL Products

The shelf life of products is the period from product manufacture to shipment to customers. The product can be unconditionally shipped within this period. The period is defined as 2 years.

If products are stored longer than the shelf life of 2 years the products shall be subjected to quality check as per CDIL quality procedure.

The products are further warranted for another one year after the date of shipment subject to the above conditions in CDIL original packing.

### Floor Life of CDIL Products and MSL Level

When the products are opened from the original packing, the floor life will start.

For this, the following JEDEC table may be referred:

JEDEC MSL Level					
Level	Time	Condition			
1	Unlimited	≤30 °C / 85% RH			
2	1 Year	≤30 °C / 60% RH			
2a	4 Weeks	≤30 °C / 60% RH			
3	168 Hours	≤30 °C / 60% RH			
4	72 Hours	≤30 °C / 60% RH			
5	48 Hours	≤30 °C / 60% RH			
5a	24 Hours	≤30 °C / 60% RH			
6	Time on Label(TOL)	≤30 °C / 60% RH			





# **Customer Notes**

### **Component Disposal Instructions**

- 1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

### Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end product), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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